Technical datasheet

1. Product Features

1.1 Electrical features

- V_{CES}=1200V
- $I_{C\ nom}$=50A / I_{CRM}=100A
- Low switching losses
- Low inductance
- Fast switching and short tail current
- Integrated NTC temperature sensor
- High power and thermal cycling capability

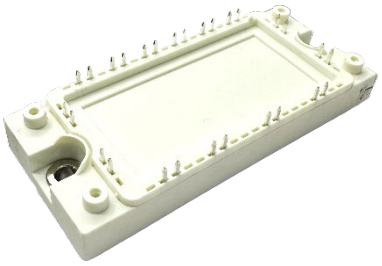


Figure 1 IGBT Module

1.2 Mechanical features

- Al_2O_3 substrate with low thermal resistance
- Copper base plate

2. Typical Applications

- Auxiliary inverters
- Motor drives
- Servo drives

3. Description

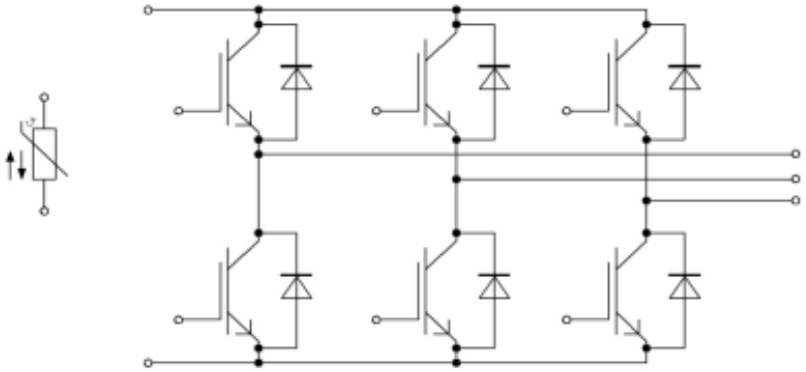


Figure 2 Half Bridge

4. IGBT, Inverter

4.1 Maximum rated values

Parameter	Note or test condition	Symbol	Values	Unit
Collector-emitter voltage 集电极—发射极间电压	Tvj = 25°C	VCES	1200	V
Continuous DC collector current 连续集电极电流	TC = 100°C, Tvj max = 150°C	IC nom	50	A
Repetitive peak collector current 集电极峰值电流	tP = 1 ms	ICRM	100	A
Total power dissipation 总功率损耗	TC = 25°C, Tvj max = 175°C	Ptot	300	W
Gate-emitter peak voltage 栅极－发射极峰值电压		VGES	+/- 20	V

4.2 Characteristic value

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage 集电极－发射极饱和电压	I_C = 50 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE,sat}$	1.5	1.7 2.0 2.1	1.9	V V V
Gate threshold voltage 栅极阈值电压	I_C = 1mA, V_{CE} = V_{GE}, T_{vj} = 25°C		$V_{GE,th}$	5.0	5.6	6.5	V
Collector-emitter cut-off current 集电极-发射极截止电流	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1	mA
Gate-emitter leakage current 栅极-发射极漏电流	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
Turn-on delay time, inductive load 开通延迟时间	I_C = 50A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,on}$ = 15Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d,on}$		0.13 0.14 0.14		us us us
Rise time, inductive load 上升时间	I_C = 50A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,on}$ = 15Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0.06 0.07 0.07		us us us

(table continues...) 待续

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time, inductive load 关断延迟时间	I_C = 50A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,off}$ = 15Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d,off}$		0.24 0.27 0.28		us us us
Fall time, inductive load 下降时间	I_C = 50A, V_{CE} = 600V V_{GE} = +15/-15V $R_{G,off}$ = 15Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0.28 0.46 0.48		us us us
Turn-on energy loss per pulse 开通损耗能量	I_C = 50A, V_{CE} = 600V, L_s=35nH V_{GE} = +15/-15V, di/dt =580A/μs $R_{G,on}$ = 15Ω (T_{vj} = 150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		6.83 9.00 9.78		mJ mJ mJ
Turn-off energy loss per pulse 关断损耗能量	I_C = 50A, V_{CE} = 600V, L_s=35nH V_{GE} = +15/-15V, dv/dt =4700A/μs $R_{G,off}$ = 15Ω (T_{vj} = 150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		3.37 4.86 5.28		mJ mJ mJ
SC data 短路数据	V_{GE} ≤15V, V_{CC} =600 V, t_P ≤ 8 μs, T_{vj} = 150°C , C_{GE} = 0.0uF , V_{CEmax} = V_{CES} - L_{sCE} · di/dt		I_{SC}		340		A
Thermal resistance, junction to case 结－外壳热阻	Per IGBT		$R_{th,JC}$			0.5	K/W

5. Diode, Inverter

5.1 Maximum rated values

Parameter	Note or test condition	Symbol	Values	Unit
Repetitive peak reverse voltage 反向重复峰值电压	T_{vj} = 25°C	V_{RRM}	1200	V
Continuous DC forward current 连续正向直流电流		I_F	50	A
Repetitive peak forward current 正向重复峰值电流	t_P = 1 ms	I_{FRM}	100	A

5.2 Characteristic value

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Forward voltage 正向电压	I_F = 50 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1.79 1.80 1.74		V V V

(table continues...) 待续

Parameter	Note or test condition		Symbol	Values			Unit
				Min.	Typ.	Max.	
Peak reverse recovery current 反向恢复峰值电流	I_F = 50A, V_R = 600V V_{GE} = -15V , - di_F/dt = 480 A/µs (T_{vj}=150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		59 68 71		A A A
Recovered charge 恢复电荷	I_F = 50A, V_R = 600V V_{GE} = -15V , - di_F/dt = 480 A/µs (T_{vj}=150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		3.6 6.3 7.4		µC µC µC
Reverse recovery energy 反向恢复损耗（每脉冲）	I_F = 50A, V_R = 600V V_{GE} = -15V , - di_F/dt = 480 A/µs (T_{vj}=150°C)	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		0.5 1.2 1.6		mJ mJ mJ
Thermal resistance, junction to case 结一外壳热阻	Per diode		$R_{th,JC}$			0.54	K/W

6. NTC-Thermistor

6.1 Characteristic value

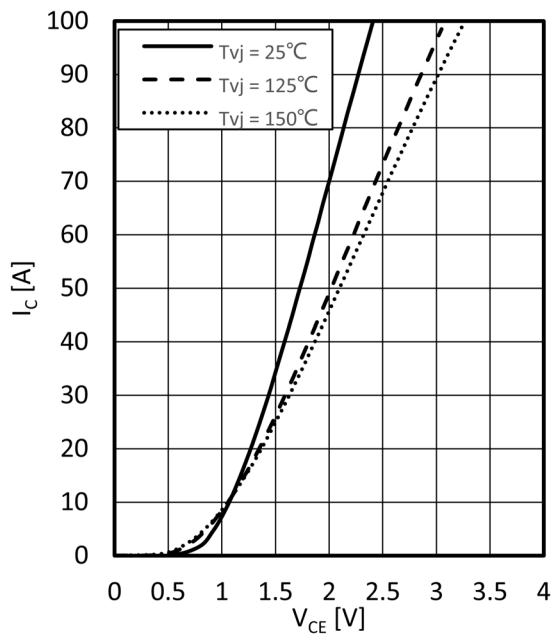
Parameter	Note or test condition	Symbol	Values			Unit
			Min.	Typ.	Max.	
Rated resistance 额定电阻值	Tc = 25°C	R_{25}		5.00		KΩ
Power dissipation 耗散功耗	Tc = 25°C	P_{25}			20	mW
B-value B-Z 值	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298, 15K))]$	B_{25}/B_{50}		3400		K
B-value B-Z 值	$R_2=R_{25}\exp[B_{25/75}(1/T_2-1/(298, 15K))]$	B_{25}/B_{75}		3430		K
B-value B-Z 值	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298, 15K))]$	B_{25}/B_{100}		3445		K

7. Module

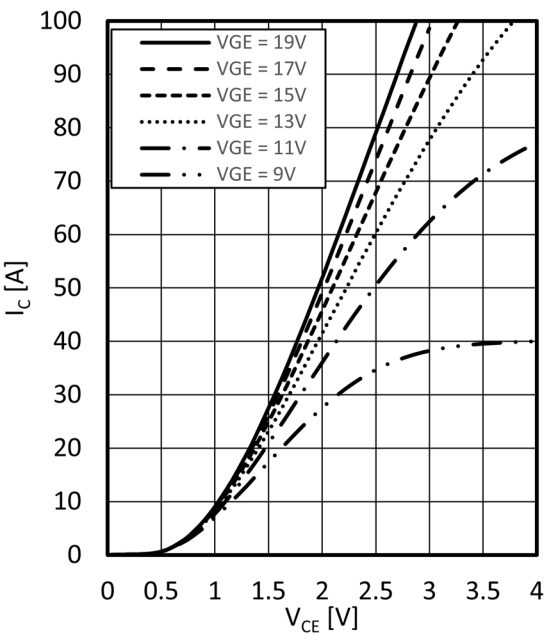
7.1 Characteristic value

Parameter	Note or test condition	Symbol	Values			Unit
			Min.	Typ.	Max.	
Isolation Voltage 隔离电压	RMS, f=50HZ,1min	V_{ISOL}			2500	V
Stray inductance module 杂散电感		L_{sCE}		20		nH
Operation Junction Temperature 结温		T_{jop}	-40		150	˚C
Storage Temperature Range 存储温度范围		T_{stg}	-40		125	˚C
Mounting Torque 安装扭矩	Screw M5	M	3		6	N.m
Weight of Module 重量		G		350		g

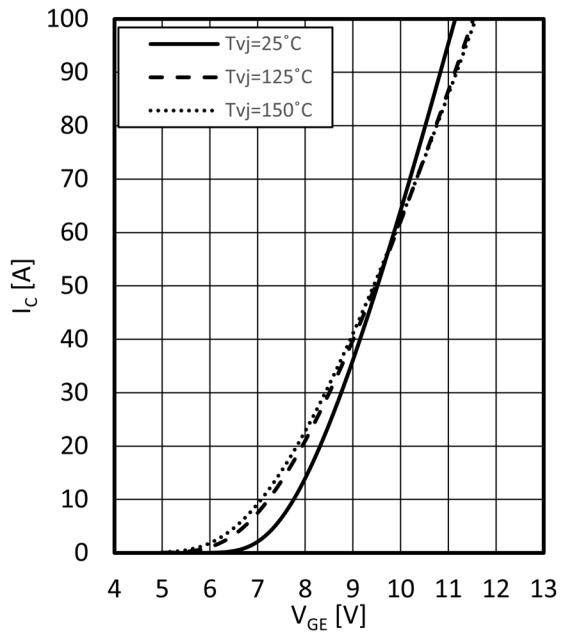
8. Characteristics diagrams



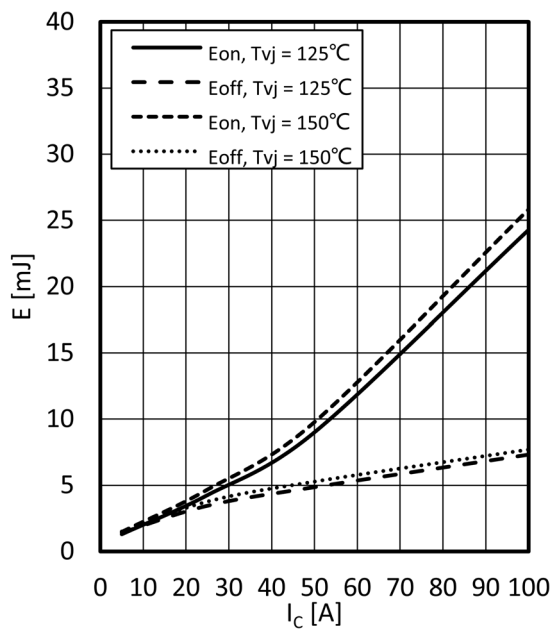
Output characteristic IGBT, Inverter (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15V$



Output characteristic IGBT, Inverter (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150°C$



Transfer characteristic IGBT, Inverter (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20V$



Switching losses IGBT, Inverter (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$R_{Goff} = 15\ \Omega$, $R_{Gon} = 15\ \Omega$, $V_{CE} = 600\ V$, $V_{GE} = \pm 15\ V$

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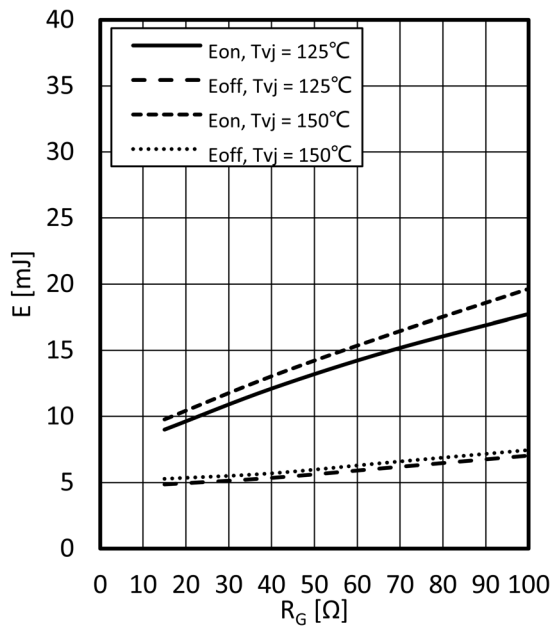
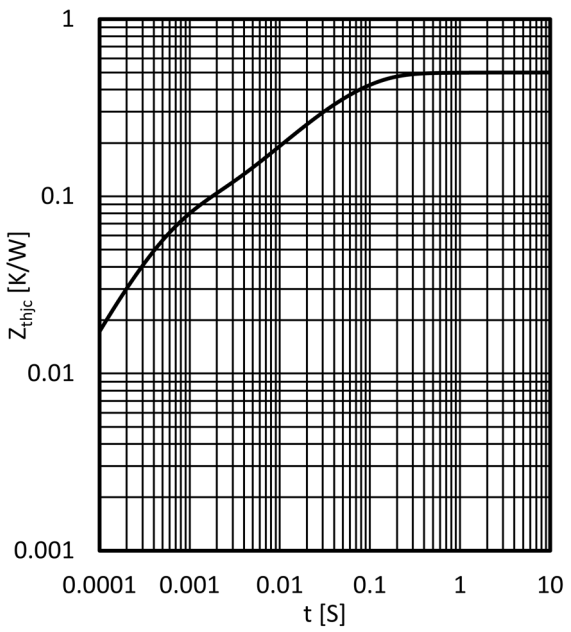
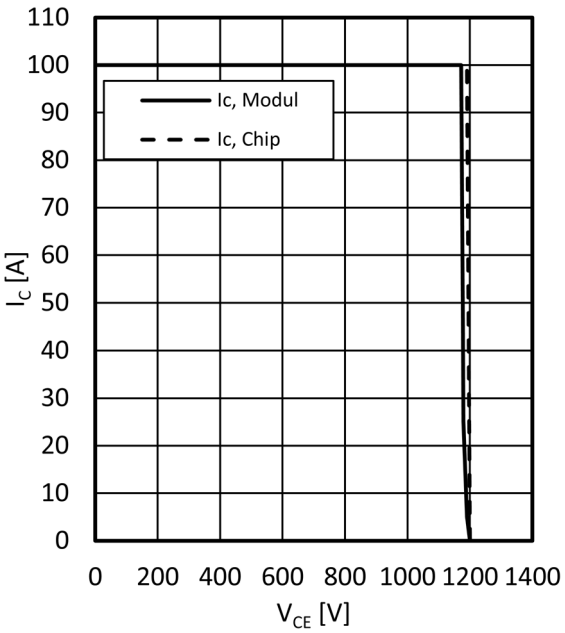


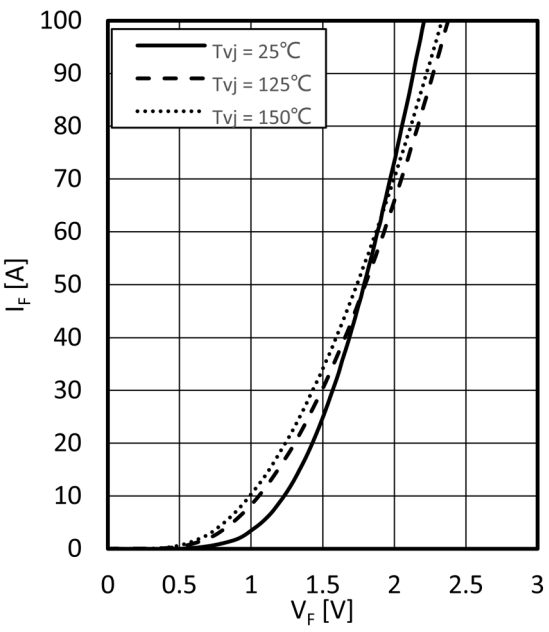
Switching losses IGBT, Inverter (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$I_C = 50$ A, $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V



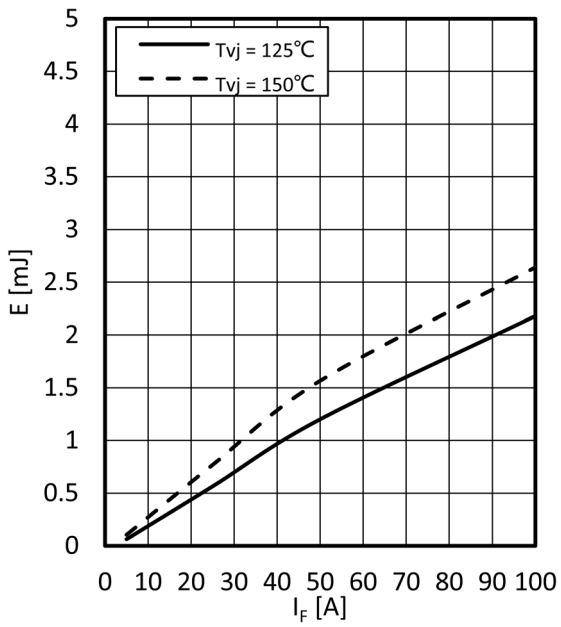
Transient thermal impedance IGBT, Inverter
$Z_{thJC} = f(t)$



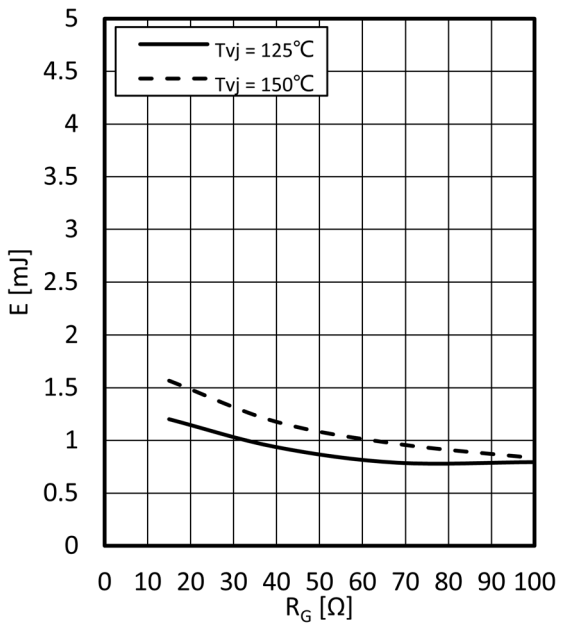
Reverse bias safe operating area IGBT, Inverter (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V, $R_{Goff} = 15\ \Omega$, $T_{vj} = 150$ °C



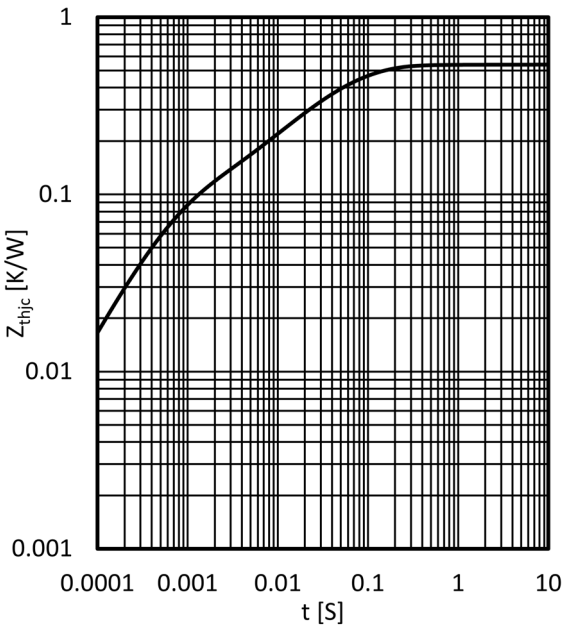
Forward characteristic of Diode, Inverter (typical)
$I_F = f(V_F)$



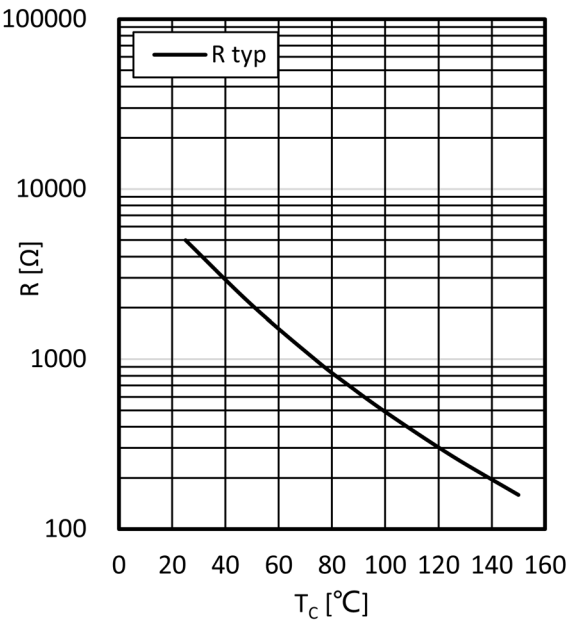
Switching losses Diode, Inverter (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 15\ \Omega$, $V_{CE} = 600\ V$



Switching losses Diode, Inverter (typical)
$E_{rec} = f(R_G)$
$I_F = 50\ A$, $V_{CE} = 600\ V$



Transient thermal impedance Diode, Inverter
$Z_{thJC} = f(t)$



NTC-Thermistor-temperature characteristic (typical)
$R = f(T_{NTC})$

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9. Circuit Diagram

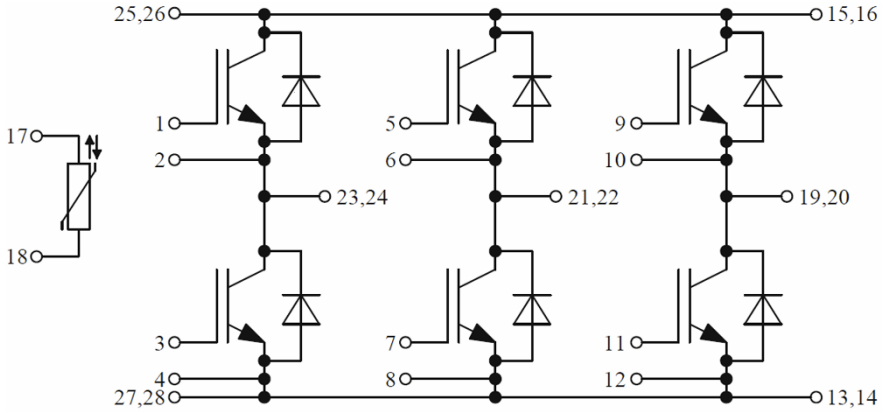

Figure 3

10. Package Outlines

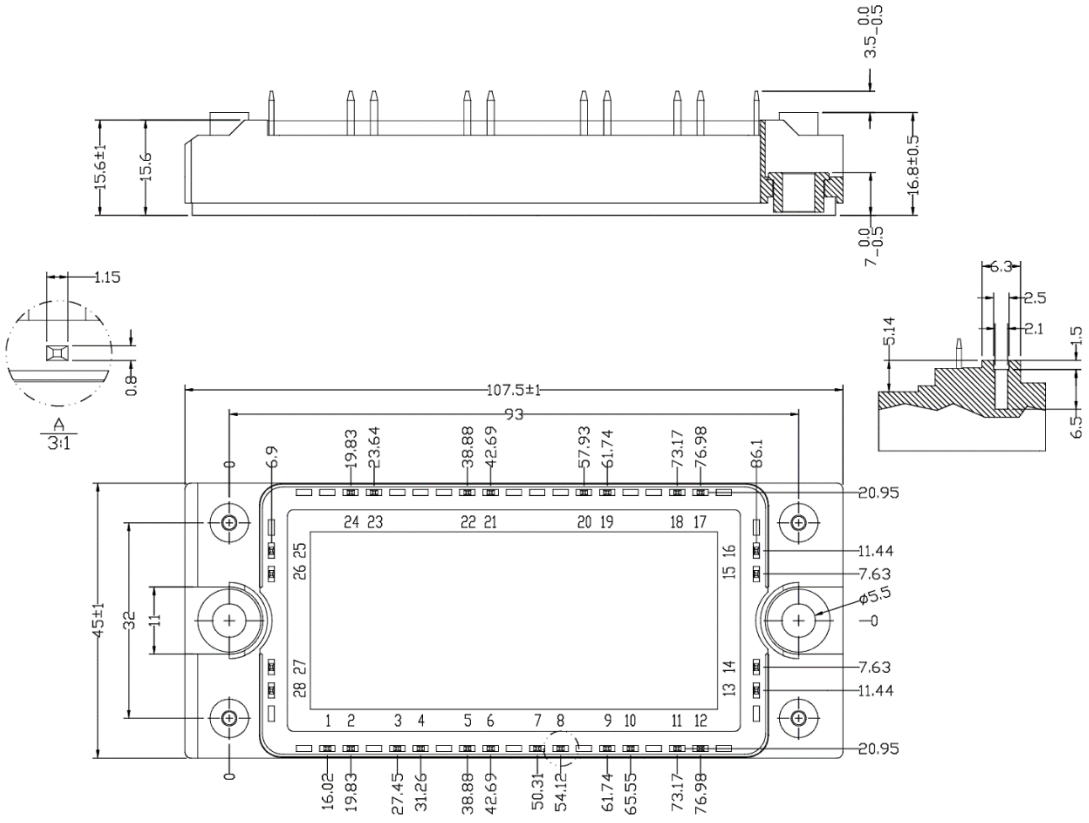

Figure 4